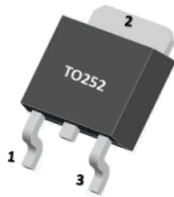


DESCRIPTION

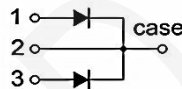
The MBR20200CS meet the ROHS and Green Product requirement with full function reliability approved.

FEATURE

- *Schottky Barrier Chip
- *Guard Ring Die Construction for Transient Protection
- *Low Power Loss,High Efficiency
- *High Surge Capability
- *High Current Capability and Low Forward Voltage Drop
- *For Use in Low Voltage, High Frequency Inverters,Free Wheeling, and Polarity Protection Applications



- 1. ANODE
- 2. CATHODE
- 3. ANODE



ABSOLUTE MAXIMUM RATINGS(TA=25°C, unless otherwise specified.)

SYMBOL	PARAMETER	VALUE	UNIT
VRRM	Peak repetitive reverse voltage	200	V
VRWM	Working peak reverse voltage	200	V
VR	DC blocking voltage	200	V
VR(RMS)	RMS reverse voltage	140	V
IO	Average rectified output current	20 (10*2)	A
IFSM	Non-Repetitive peak forward surge current(8.3ms half sine wave)	150*2	A
Tj	Junction temperature	175	°C
Tstg	Storage temperature	-55 ~ +150	°C
Cj (Ctot)	Typical total capacitance VR=5V,f=1MHz	500	pF
RθJA	Thermal Resistance from Junction to Ambient	100	°C/W
RθJC	Thermal Resistance From Junction To Case	5	°C/W

Notes: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (TA=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reverse voltage	V _(BR)	I _R =0.1mA	200			V
Reverse current	I _R	V _R =200V	T _J =25°C	0.5	3	uA
			T _J =125°C	2.0		mA
Forward voltage	V _F	I _F =5A	T _J =25°C	0.78		V
			T _J =125°C	0.66		V
		I _F =10A	T _J =25°C	0.86	0.92	V
			T _J =125°C	0.74		V

Pulse test: pulse width ≤300μs, duty cycle≤ 2.0%.

■ TYPICAL CHARACTERISTICS

FIG.1: FORWARD CURRENT DERATING CURVE

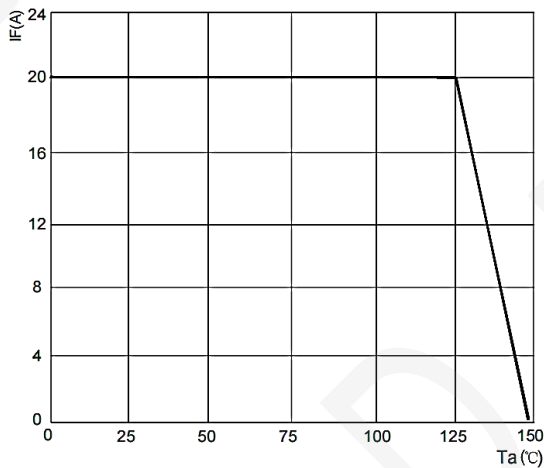


FIG.2: TYPICAL FORWARD CHARACTERISTICS

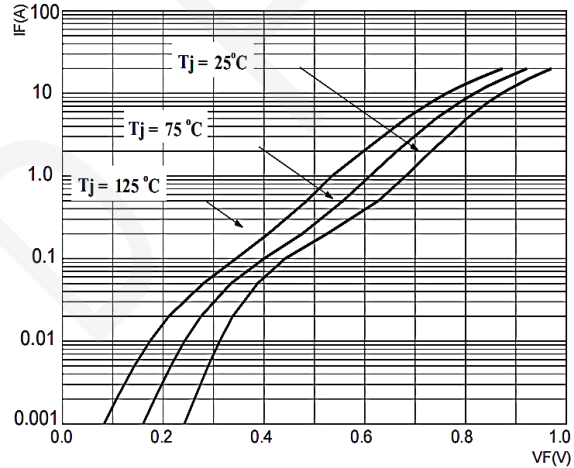


FIG.3: TOTAL CAPACITANCE DERATING CURVE

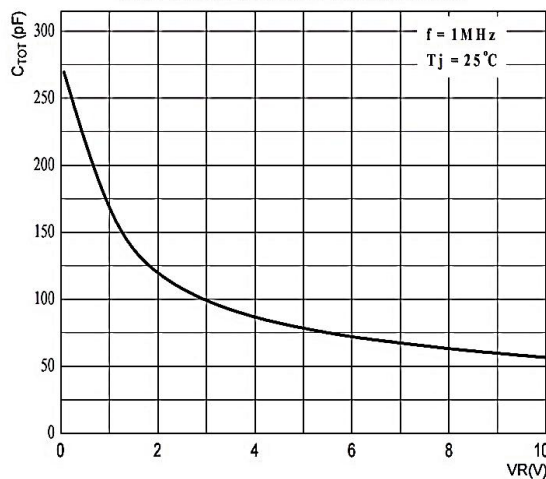


FIG.4: TYPICAL REVERSE CHARACTERISTICS

